

0039-6348-2SRD REISSUE

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE REISSUE OF U.S. PATENT NO: 5,570,315

PATENTEE: TOMOHARU TANAKA ET AL :

SERIAL NO: 09/134,897

: GROUP ART UNIT: 2824

FILED: AUGUST 17, 1998

: EXAMINER: TRAN

FOR: MULTI-STATE EEPROM ~~DATA~~ ~~ERASE~~
WRITE-VERIFY CONTROL CIRCUIT



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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Office Action mailed November 20, 2000, please amend
the above-identified application as follows:

IN THE CLAIMS

**Please amend the claims as shown in the attachment. A complete set of claims in
clean form is shown below.**

Please cancel without prejudice Claims 130-132, 136-138, 141-142 and 144-149.

Please amend Claims 120, 121, 123, 125, 127, 129, 133, 139, 143 and 150 as follows:

120. (Amended) A multilevel nonvolatile semiconductor memory device comprising:
a NAND-cell unit including a plurality of memory cells connected in series, each of
said memory cells including a transistor with a control gate and a charge storage portion and
having storage states of at least three threshold voltage levels;